

IMPROVED METHOD OF METAL PLATING SEMICONDUCTORS

Abstract of the Disclosure

A metal underlayer is selectively plated on semiconductor wafers immediately followed by plating copper on the metal underlayer using a low internal stress copper plating bath. Additional metallization may be done to build up the metal layers using conventional metal plating baths and methods to form current tracks. Formation of metal silicides is avoided. Good adhesion of the metals to the semiconductors is achieved. The metalized semiconductors may be used in the manufacture of photovoltaic devices.

No Figure